

A METHOD AND STRUCTURE FOR LOW CAPACITANCE ESD ROBUST DIODES

Abstract of the Disclosure

A diode having a capacitance below 0.1pF and a breakdown voltage of at least 500V. The diode has an anode of a first conductivity type and a cathode of a second conductivity type disposed below the anode. At least one of the cathode and anode have multiple, vertically abutting diffusion regions. The cathode and anode are disposed between and bounded by adjacent isolation regions.

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Figures

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